

SYSTEMS AND METHODS FOR HIGH TEMPERATURE PROCESSING OF SEMICONDUCTOR WAFERS

ABSTRACT OF THE DISCLOSURE

5 The present invention provides systems, methods and apparatus for
high temperature (at least about 500-800°C) processing of semiconductor wafers.
The systems, methods and apparatus of the present invention allow multiple process
steps to be performed in situ in the same chamber to reduce total processing time
and to ensure high quality processing for high aspect ratio devices. Performing
10 multiple process steps in the same chamber also increases the control of the process
parameters and reduces device damage. In particular, the present invention can
provide high temperature deposition, heating and efficient cleaning for forming
dielectric films having thickness uniformity, good gap fill capability, high density,
low moisture, and other desired characteristics.

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